AMENDMENTS TO THE CLAIMS

1. (Previously Presented) A liquid crystal display device, comprising:

a display panel including a lower layer at the lowest portion of the display panel and an uppermost layer, positioned above the lowest layer at the uppermost portion of said display panel;

a first substrate forming said uppermost layer of said display panel, including:

a) a switching element on the first substrate, said switching element being connected to a gate line and a data line, the switching element being a thin film transistor having a gate electrode formed on the first substrate, a gate insulating layer formed on an exposed surface of the first substrate while covering the gate electrode, an active layer on the gate insulating layer over the gate electrode, an ohmic contact layer on the active layer, a source electrode on the ohmic contact layer, a drain electrode on the ohmic contact layer, and a first light absorbing film under the gate electrode;

b) a passivation film formed over the whole surface of the first substrate while covering the switching element;

c) a pixel electrode on the passivation film;

d) a black matrix formed on the passivation film and over the switching element;

e) a color filter formed over the pixel electrode; and

f) a first orientation film formed on the black matrix and the color filter and above the pixel electrode;

a second substrate having no switching element disposed thereon, forming said lowest portion of the display panel, said second substrate being aligned with the first substrate, said second substrate having a common electrode and a second orientation film, said second orientation film being formed on the common electrode;

a sealant for sealing said first and second substrates;

a liquid crystal layer interposed between said first and second substrates; and

a backlight device disposed beneath said second substrate such that said second substrate is located between said backlight device and said first substrate.

2. (Previously Presented) The liquid crystal display device of claim 1, wherein the source electrode overlaps one end portion of the active layer, and the drain electrode overlaps the other end portion of the active layer.

3. (Previously Presented) The liquid crystal display device of claim 2, further comprising a second light absorbing film formed under the source electrode, and a third light absorbing film formed under the drain electrode.

4. (Previously Presented) The liquid crystal display device of claim 2, further comprising a second light absorbing film formed under the semiconductor layer.

5. (Previously Presented) The liquid crystal display device of claim 3, further comprising, the first light absorbing film formed under the gate line, and the second light absorbing film formed under data line.

6. (Previously Presented) The liquid crystal display device of claim 4, further comprising, the first light absorbing film formed under the gate line, and the second light absorbing film formed under data line.

7. (Previously Presented) The liquid crystal display device of claim 5, wherein the back light device is for supplying light to the liquid crystal layer.

8. (Original) The liquid crystal display device of claim 7, wherein the common electrode and the pixel electrode are made of indium tin oxide (ITO).

9-11. (Canceled)

12. (Previously Presented) A method of manufacturing a liquid crystal display device which comprises an array of thin film transistors, an array of pixel electrodes and a backlight device, said method including:

forming a gate line and a gate electrode on a first substrate said first substrate forming the uppermost layer of a display panel, the gate electrode extending from the gate line;

forming a gate insulating layer on the exposed surface of the upper substrate while covering the gate line and the gate electrode;

forming an active layer on the gate insulating layer over the gate electrode;

forming an ohmic contact layer on the active layer;

forming a data line and source and drain electrodes, the source electrode on the ohmic contact layer and overlapping one end portion of the active layer, the drain electrode on the ohmic contact layer and overlapping the other end portion of the active layer, the source and drain electrodes spaced apart from each other, the source electrode extending from the data line, said gate, source and drain electrodes comprising a thin film transistor formed on said first substrate;

forming a first light absorbing film under the gate electrode;

forming a passivation film over the whole surface of the first substrate while covering the source and drain electrodes, the passivation film having a contact hole on the drain electrode;

forming a pixel electrode on the passivation film, the pixel electrode electrically connected with the drain electrode through the contact hole;

forming a color filter on the pixel electrode;

forming a black matrix over the thin film transistor;

forming a first orientation film on the color filters and the black matrices;

forming a common electrode on a second substrate;

forming a second orientation film on the common electrode;

aligning the first substrate turned upside down with the second substrate with a gap between the first substrate and the second substrate so that the thin film transistor is also turned

upside down and the first orientation film of the first substrate is opposite to the second orientation film of the second substrate ;

sealing the first and second substrates with a sealant;

injecting a liquid crystal between the first substrate and the second substrate; and

positioning said backlight device beneath said second substrate such that said second substrate is located between said backlight device and said first substrate.

13. (Previously Presented) The method of claim 12, further comprising:

forming the first light absorbing film between the first substrate and the gate electrode; and

forming a second light absorbing film between the active layer and the source and drain electrodes.

14. (Previously Presented) The method of claim 12, further comprising:

forming the first light absorbing film between the first substrate and the gate electrode; and

forming a second light absorbing film between the active layer and the gate insulating layer.

15. (Original) The method of claim 13, wherein the common electrode and the pixel electrode are made of indium tin oxide.

16. (Original) The method of claim 14, wherein the common electrode and the pixel electrode are made of indium tin oxide.

17-18. (Canceled)

19. (Original) The liquid crystal display device of claim 7, wherein the common electrode and the pixel electrode are made of a transparent material.

20. (Previously Presented) The method of claim 13, wherein the common electrode and the pixel electrode are made of a transparent material.

21. (Previously Presented) The liquid crystal display device of claim 3, wherein the light absorbing films absorb natural incident light to reduce reflected light dazzle.

22. (Previously Presented) The method of claim 13, wherein the light absorbing films absorb natural incident light to reduce reflected light dazzle.

23. (Previously Presented) The method of claim 14, wherein the light absorbing films absorb natural incident light to reduce reflected light dazzle.

24. (Previously Presented) The liquid crystal display device of claim 3, wherein the light absorbing films each comprise a low reflectance material selected from the group consisting of an oxidation film, a nitride film and a black resin.

25. (Previously Presented) The method of claim 13, wherein the light absorbing films each comprise a low reflectance material selected from the group consisting of an oxidation film, a nitride film and a black resin.

26. (Previously Presented) The method of claim 14, wherein the light absorbing films each comprise a low reflectance material selected from the group consisting of an oxidation film, a nitride film and a black resin.

27. (New) A liquid crystal display device, comprising:

a display panel including a lower layer at the lowest portion of the display panel and an uppermost layer, positioned above the lowest layer at the uppermost portion of said display panel;

a first substrate forming said uppermost layer of said display panel, including:

a) a switching element on the first substrate, said switching element being connected to a gate line and a data line, the switching element being a thin film transistor having a gate electrode formed on the first substrate, a gate insulating layer formed on an exposed surface of the first substrate while covering the gate electrode, an active layer on the gate insulating layer over the gate electrode, an

ohmic contact layer on the active layer, a source electrode on the ohmic contact layer, a drain electrode on the ohmic contact layer, and a first light absorbing film under the gate electrode;

b) a passivation film formed over the whole surface of the first substrate while covering the switching element;

c) a pixel electrode on the passivation film;

d) a black matrix formed on the passivation film and over the switching element;

e) a color filter formed over the pixel electrode; and

f) a first orientation film formed on the black matrix and the color filter and above the pixel electrode;

a second substrate having no switching element disposed thereon, forming said lowest portion of the display panel, said second substrate being aligned with the first substrate, said second substrate having a common electrode and a second orientation film, said second orientation film being formed on the common electrode;

a sealant for sealing said first and second substrates;

a liquid crystal layer interposed between said first and second substrates; and

a backlight device disposed beneath said second substrate as a light source such that said second substrate is located between said backlight device and said first substrate, and the black matrix is inserted between the light source and the thin film transistor on the first substrate.

28. (New) A method of manufacturing a liquid crystal display device which comprises an array of thin film transistors, an array of pixel electrodes and a backlight device as a light source, said method comprising:

forming a gate line and a gate electrode on a first substrate said first substrate forming the uppermost layer of a display panel, the gate electrode extending from the gate line;

forming a gate insulating layer on the exposed surface of the upper substrate while covering the gate line and the gate electrode;

forming an active layer on the gate insulating layer over the gate electrode;

forming an ohmic contact layer on the active layer;

forming a data line and source and drain electrodes, the source electrode on the ohmic contact layer and overlapping one end portion of the active layer, the drain electrode on the ohmic contact layer and overlapping the other end portion of the active layer, the source and drain electrodes spaced apart from each other, the source electrode extending from the data line, said gate, source and drain electrodes comprising a thin film transistor formed on said first substrate;

forming a first light absorbing film under the gate electrode;

forming a passivation film over the whole surface of the first substrate while covering the source and drain electrodes, the passivation film having a contact hole on the drain electrode;

forming a pixel electrode on the passivation film, the pixel electrode electrically connected with the drain electrode through the contact hole;

forming a color filter on the pixel electrode;

forming a black matrix over the thin film transistor;

forming a first orientation film on the color filters and the black matrices;

forming a common electrode on a second substrate;

forming a second orientation film on the common electrode;

aligning the first substrate turned upside down with the second substrate with a gap between the first substrate and the second substrate so that the thin film transistor is also turned upside down and the first orientation film of the first substrate is opposite to the second orientation film of the second substrate;

sealing the first and second substrates with a sealant;

injecting a liquid crystal between the first substrate and the second substrate; and

positioning said backlight device beneath said second substrate such that said second substrate is located between said backlight device and said first substrate, and the black matrix is inserted between the light source and the thin film transistor on the first substrate.